

# MMBA812M6

# PNP EPITAXIAL SILICON TRANSISTOR

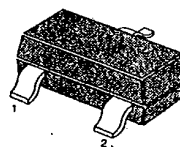
## GENERAL PURPOSE TRANSISTOR

## ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

| Characteristic            | Symbol    | Rating | Unit             |
|---------------------------|-----------|--------|------------------|
| Collector-Base Voltage    | $V_{CB0}$ | 50     | V                |
| Collector-Emitter Voltage | $V_{CE0}$ | 40     | V                |
| Emitter-Base Voltage      | $V_{EB0}$ | 5      | V                |
| Collector Current         | $I_C$     | 100    | mA               |
| Collector Dissipation     | $P_C$     | 350    | mW               |
| Storage Temperature       | $T_{stg}$ | 150    | $^\circ\text{C}$ |

• Refer to MMBT5086 for graphs

SOT-23



1. Base 2. Emitter 3. Collector

## ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )

| Characteristic                       | Symbol        | Test Condition                     | Min | Max | Unit |
|--------------------------------------|---------------|------------------------------------|-----|-----|------|
| Collector Cutoff Current             | $I_{CBO}$     | $V_{CB}=40\text{V}, I_E=0$         |     | 100 | nA   |
| Emitter Cutoff Current               | $I_{EBO}$     | $V_{EB}=5\text{V}, I_C=0$          |     | 100 | nA   |
| DC Current Gain                      | $h_{FE}$      | $V_{CE}=6\text{V}, I_C=1\text{mA}$ | 200 | 400 |      |
| Collector-Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C=30\text{mA}, I_B=3\text{mA}$  |     | 0.5 | V    |
| Base-Emitter On Voltage              | $V_{BE(on)}$  | $I_C=1\text{mA}, V_{CE}=6\text{V}$ |     | 0.8 | V    |

Marking

